

ABSTRACT OF THE DISCLOSURE

The present invention employs a no mask, blanket implant of an n-type implant after formation of active regions in NMOS devices. As a result, the implanted n-type dopants counteract portions of strongly p-type HALO or pocket regions creating a smoother dopant profile or transition from a portion of the active regions to the channel. However, the blanket implant is performed at a relatively low energy so as to not significantly alter one or more other portions of the active regions to other portions of the device.

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